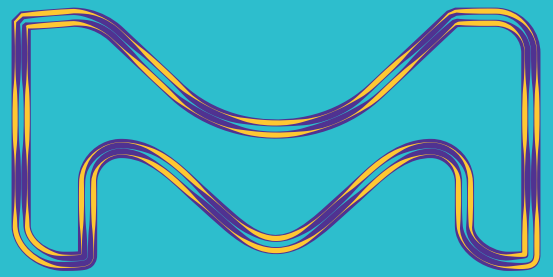
AZ EXP LNR-003

Suggested Modifications

for smaller Film Thicknesses (1.5 µm)



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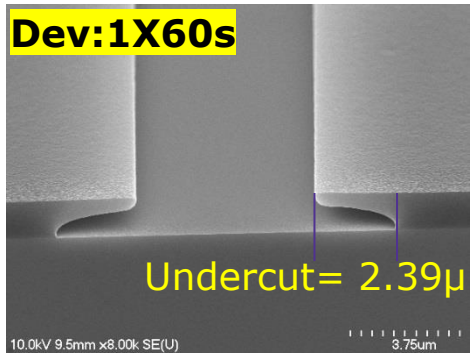
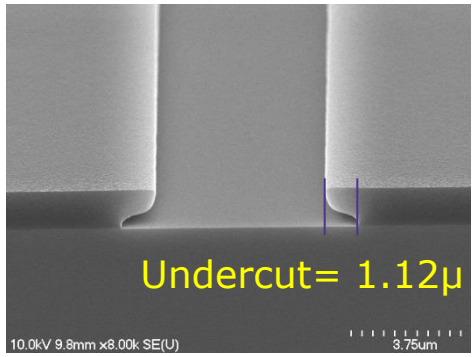
AZ Exp LNR-003

FT: 1.5µ
SB:100°C/90s
PEB:100°C/90s
ASML i-line
NA 0.48 stepper
F=1µ
Mask CD: Iso Trench 5µ

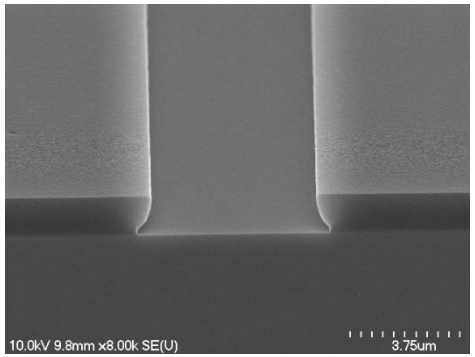
50mJ/cm²



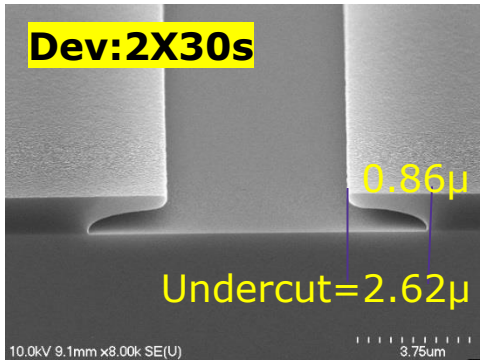
60mJ/cm²



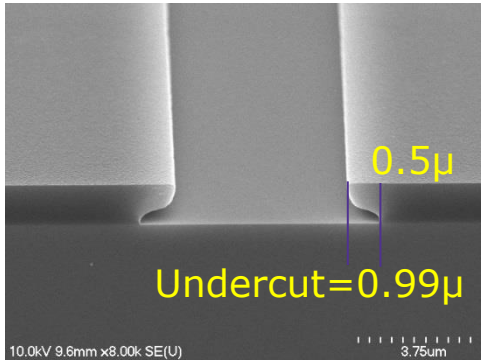
70mJ/cm²



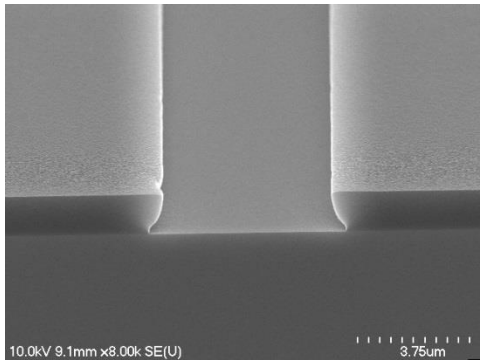
50mJ/cm²



60mJ/cm²



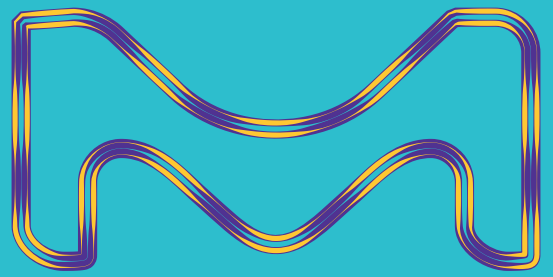
70mJ/cm²



AZ EXP LNR-003

Suggested Modifications

for smaller Film Thicknesses (1.0 µm)



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AZ Exp LNR-003

Process Conditions

- **Substrate**: Si-wafer
- **FT**: 0.98µ
- **SB**: 110ºC/ 60s
- **Exposure**: ASML i-line; NA 0.6 stepper
- **Focus**: 0µ
- **PEB**: Varied
- **Spin Speed**: 2500rpm/30s
- **Development**: 30s, AZ 300 MIF developer
- **Mask CD**: Isolated Trenches: 0.6µ

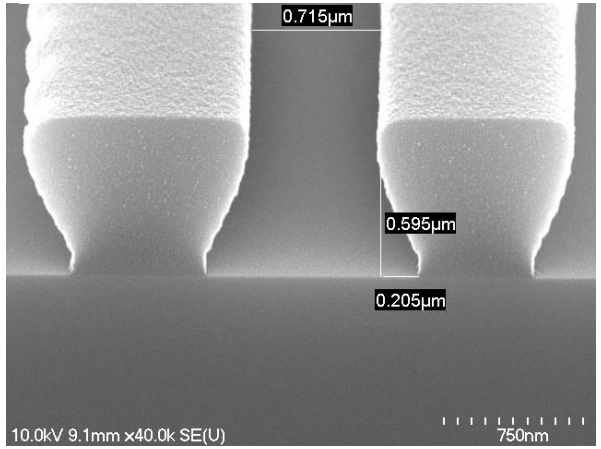
AZ Exp LNR-003

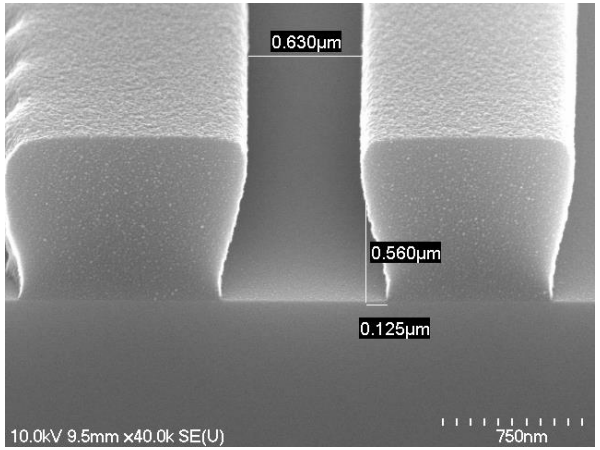
FT	SB	Dev	Mask CD	Exposure	NA	Parameter Varied
1µ	100ºC/60s	30s	Iso Trench: 0.3µ	i-line stepper F=0µ	0.6	PEB

70 mJ/cm²

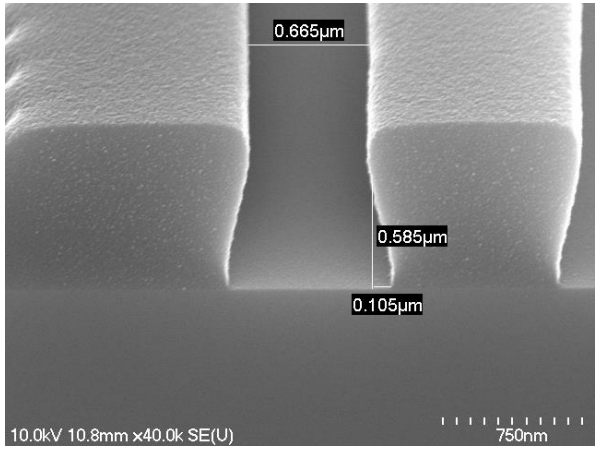
80 mJ/cm²

PEB:105ºC/60s





PEB:110ºC/60s



AZ Exp LNR-003

FT	SB	Dev	Mask CD	Exposure	NA	PEB	Dose
1µ	100ºC/60s	30s	Iso Trench: 0.3µ	i-line stepper F=0µ	0.6	110ºC/60s	70mJ/cm^2

Mask CD: **0.22µ** **0.28µ** **0.30µ** **0.38µ**